

酸化物半導体(加藤研究員_産総研、高木教授_東京大学)の関連論文

1. K. Kato, et al., "Fabrication and electrical characteristics of ZnSnO/Si bilayer tunneling field-effect transistors," to be published in IEEE J. Electron Devices Society.
2. K. Kato, et al., "Material design of oxide-semiconductor/group-IV-semiconductor bilayer tunneling field effect transistors," 3rd Electron Devices Technology and Manufacturing (EDTM), Singapore, March 2019, pp. 85-87.
3. K. Kato et al., "ZnO/Si and ZnO/Ge bilayer tunneling field effect transistors: Experimental characterization of electrical properties," J. Appl. Phys., 125(19), 195701(1-10), May 2019.
4. K. Kato et al., "Bilayer tunneling field effect transistor with oxide-semiconductor and group-IV semiconductor hetero junction: Simulation analysis of electrical characteristics," AIP Adv., 9(5), 055001(1-11), May 2019.
5. K. Kato, et al., "Proposal and demonstration of oxide-semiconductor/(Si, SiGe, Ge) bilayer tunneling field effect transistor with type-II energy band alignment," Int. Electron Devices Meeting, Dec. 2017, pp. 377-380.
6. K. Kato, et al., "TiN/Al₂O₃/ZnO gate stack engineering for top-gate thin film transistors by combination of post oxidation and annealing," Appl. Phys. Lett., 112(16), 162105(1-4) (2018).